







SN74LVC1T45-Q1

SCES677F - SEPTEMBER 2006 - REVISED JUNE 2024

SN74LVC1T45-Q1 Automotive 1.65V to 5.5V Single-Bit Dual-Supply Level Shifter

1 Features

- Qualified for automotive applications
- AEC-Q100 qualified with the following results:
 - Device temperature grade 1: -40°C to +125°C ambient operating temperature range
 - Device HBM ESD Classification Level H2
 - Device CDM ESD Classification Level C3B
- Fully configurable dual-rail design allows each port to operate over the full 1.65V to 5.5V power-supply
- V_{CC} isolation feature if either V_{CC} input is at GND, both ports are in the high-impedance state
- DIR input circuit referenced to V_{CCA}
- ±24mA output drive at 3.3V
- I_{off} supports partial-power-down mode operation
- Maximum data rates:
 - 420Mbps (3.3V to 5V translation)
 - 210Mbps (translate to 3.3V)
 - 140Mbps (translate to 2.5V)
 - 75Mbps (translate to 1.8V)

2 Applications

- Head units
- ADAS cameras
- **Telematics**

3 Description

The SN74LVC1T45-Q1 device is a single-bit, noninverting bus transceiver that uses two separate configurable power supply rails. The A-port is designed to track V_{CCA}. V_{CCA} accepts any supply voltage from 1.65V to 5.5V. The B-port is designed to track V_{CCB}. V_{CCB} accepts any supply voltage from 1.65V to 5.5V. This allows for universal low-voltage bidirectional translation between any of the 1.8V, 2.5V, 3.3V, and 5V voltage nodes.

The SN74LVC1T45-Q1 device is a single-bit, noninverting level translator. The fully configurable dualrail design allows each port to overate over the full 1.65V to 5.5V power supply range. This device is an excellent choice for applications that need a wide bidirectional translation range.

The SN74LVC1T45-Q1 is designed so that the DIR input is powered by V_{CCA}.

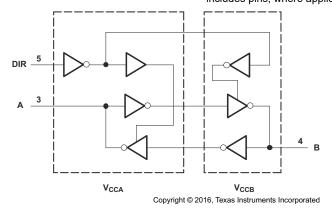
This device is fully specified for partial-power-down applications using Ioff. The Ioff circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

The V_{CC} isolation feature is designed so that if either V_{CC} input is at GND, then both ports are in the highimpedance state.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE ⁽²⁾
SN74LVC1T45-Q1	DCK (SC70, 6)	2mm × 2.1mm

- For more information, see Section 9
- The package size (length × width) is a nominal value and includes pins, where applicable.



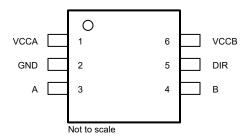
Logic Diagram (Positive Logic)



Table of Contents

1 Features1	6 Detailed Description12
2 Applications 1	6.1 Overview
B Description1	6.2 Functional Block Diagram12
4 Pin Configuration and Functions2	6.3 Feature Description12
5 Specifications3	6.4 Device Functional Modes12
5.1 Absolute Maximum Ratings3	7 Device and Documentation Support17
5.2 ESD Ratings3	7.1 Documentation Support17
5.3 Recommended Operating Conditions3	7.2 Receiving Notification of Documentation Updates 17
5.4 Thermal Information4	7.3 Support Resources17
5.5 Electrical Characteristics5	7.4 Trademarks17
5.6 Switching Characteristics: V _{CCA} = 1.8V ±0.15V6	7.5 Electrostatic Discharge Caution17
5.7 Switching Characteristics: V _{CCA} = 2.5V ±0.2V6	7.6 Glossary17
5.8 Switching Characteristics: V _{CCA} = 3.3V ±0.3V7	8 Revision History17
5.9 Switching Characteristics: V _{CCA} = 5V ±0.5V7	9 Mechanical, Packaging, and Orderable Information 17
5 10 Typical Characteristics 8	

4 Pin Configuration and Functions



See mechanical drawings for dimensions.

Figure 4-1. DCK Package, 6-Pin SC70 (Top View)

Table 4-1. Pin Functions

PI	N	TYPE ⁽¹⁾	DESCRIPTION				
NAME	NO.	ITPE\/	DESCRIPTION				
Α	3	I/O	Output level depends on V _{CC1} voltage				
В	B 4		Input threshold value depends on V _{CC2} voltage				
DIR	5	I	GND (low level) determines B-port to A-port direction				
GND	2	G	Device GND				
V _{CCA} 1		Р	SYSTEM-1 supply voltage (1.65V to 5.5V)				
V _{CCB}	V _{CCB} 6		SYSTEM-2 supply voltage (1.65V to 5.5V)				

(1) G = Ground, I = Input, O = Output, P = Power

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
Supply voltage, V _{CCA} , V _{CCB}		-0.5	6.5	V
Input voltage, V _I ⁽²⁾		-0.5	6.5	V
Voltage applied to any output in the high-impedance or power-off state, Vo	o ⁽²⁾	-0.5	6.5	V
/oltage applied to any output in the high or low state, V _O ^{(2) (3)} A port B port		-0.5	V _{CCA} + 0.5	V
		-0.5	V _{CCB} + 0.5	v
Input clamp current, I _{IK} (V _I < 0)			– 50	mA
Output clamp current, I _{OK} (V _O < 0)			<i>–</i> 50	mA
Continuous output current, I _O			±50	mA
Continuous current through V _{CC} or GND			±100	mA
Junction temperature, T _J			150	°C
Storage temperature, T _{stg}		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- (2) The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- 3) The value of V_{CC} is provided in *Recommended Operating Conditions*.

5.2 ESD Ratings

			VALUE	UNIT
\ <u>\</u>		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±750	V

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
- 2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

See(1) (2) (3)

			MIN	MAX	UNIT
V _{CCA}	Supply voltage		1.65	5.5	V
V _{CCB}	Supply voltage		1.65	5.5	V
		V _{CCI} = 1.65V to 1.95V	V _{CCI} × 0.65		
	High-level input voltage,	V _{CCI} = 2.3V to 2.7V	1.7		V
V _{IH}	data inputs ⁽⁴⁾	V _{CCI} = 3V to 3.6V	2		V
		V _{CCI} = 4.5V to 5.5V	V _{CCI} × 0.7		
		V _{CCI} = 1.65V to 1.95V		V _{CCI} × 0.35	
,,	Low-level input voltage,	V _{CCI} = 2.3V to 2.7V		0.7	V
V _{IL}	data inputs ⁽⁴⁾	V _{CCI} = 3V to 3.6V		0.8	V
		V _{CCI} = 4.5V to 5.5V		V _{CCI} × 0.3	
		V _{CCI} = 1.65V to 1.95V	V _{CCA} × 0.65		
V	High-level input voltage,	V _{CCI} = 2.3V to 2.7V	1.7		V
V _{IH}	DIR (referenced to V _{CCA}) ⁽⁵⁾	V _{CCI} = 3V to 3.6V	2		V
		V _{CCI} = 4.5V to 5.5V	V _{CCA} × 0.7		

5.3 Recommended Operating Conditions (continued)

See(1)(2)(3)

				MIN	MAX	UNIT	
			V _{CCI} = 1.65V to 1.95V	V	_{CCA} × 0.35		
V _{IL} V _I V _O I _{OH} Δt/Δv	Low-level input voltage, DIR (referenced to V _{CCA}) ⁽⁵⁾		V _{CCI} = 2.3V to 2.7V		0.7	V	
			V _{CCI} = 3V to 3.6V	V _{CCI} = 3V to 3.6V		v	
. 33.0			V _{CCI} = 4.5V to 5.5V		V _{CCA} × 0.3		
VI	Input voltage			0	5.5	V	
Vo	Output voltage			0	V _{cco}	V	
			V _{CCO} = 1.65V to 1.95V		-4		
I _{OH}	High-level output current		V _{CCO} = 2.3V to 2.7V		-8	mA	
			V _{CCO} = 3V to 3.6V		-24	ША	
			V _{CCO} = 4.5V to 5.5V		-32		
			V _{CCO} = 1.65V to 1.95V		4		
	Low lovel output ourror	.+	V _{CCO} = 2.3V to 2.7V		8	mΛ	
OL	Low-level output curren	ıı	V _{CCO} = 3V to 3.6V		24	mA	
			V _{CCO} = 4.5V to 5.5V		32		
			V _{CCI} = 1.65V to 1.95V		20		
		Data innuta	V _{CCI} = 2.3V to 2.7V		20		
Δt/Δν	Input transition rise or fall rate	Data inputs	V _{CCI} = 3V to 3.6V		10	ns/V	
	nee or fair rate		V _{CCI} = 4.5V to 5.5V		5		
		Control inputs, V _{CC}	Control inputs, V _{CCI} = 1.65V to 5.5V		5		
T _A	Operating free-air temp	erature		-40	125	°C	

- (2)
- V_{CCI} is the V_{CC} associated with the input port. V_{CCO} is the V_{CC} associated with the output port. All unused data inputs of the device must be held at V_{CCI} or GND for proper device operation. See *Implications of Slow or Floating* CMOS Inputs (SCBA004).
- (4) For V_{CCI} values not specified in the data sheet, V_{IH} min = V_{CCI} × 0.7V, V_{IL} max = V_{CCI} × 0.3V.
 (5) For V_{CCI} values not specified in the data sheet, V_{IH} min = V_{CCA} × 0.7V, V_{IL} max = V_{CCA} × 0.3V.

5.4 Thermal Information

		SN74LVC1T45-Q1	
	THERMAL METRIC(1)	DCK (SC70)	UNIT
		6 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	210.9	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	139.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	72	°C/W
ΨЈТ	Junction-to-top characterization parameter	54.9	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	71.7	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	_	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

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5.5 Electrical Characteristics

over operating free-air temperature range with all limits at $T_A = -40$ °C to 125°C (unless otherwise noted)⁽¹⁾ (2)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT	
		I _{OH} = -100 μA, V _{CCA} = 1 V _{CCB} = 1.65V to 4.5V	.65V to 4.5V,	V _{CCO} - 0.1				
		I _{OH} = -4mA, V _{CCA} = 1.65	1.2					
V _{OH}	$V_I = V_{IH}$	$I_{OH} = -8mA, V_{CCA} = 2.3V$	/, V _{CCB} = 2.3V	1.9			V	
		$I_{OH} = -24 \text{mA}, V_{CCA} = 3 \text{V}$, V _{CCB} = 3V	2.3				
		$I_{OH} = -32 \text{mA}, V_{CCA} = 4.5$	5V, V _{CCB} = 4.5V	3.8				
		I _{OL} = 100 μA, V _{CCA} = 1.6 V _{CCB} = 1.65V to 4.5V	5V to 4.5V,			0.1		
		I _{OL} = 4mA, V _{CCA} = 1.65V	', V _{CCB} = 1.65V			0.45		
V _{OL}	$V_I = V_{IL}$	$I_{OL} = 8mA, V_{CCA} = 2.3V,$	V _{CCB} = 2.3V			0.4	V	
		I _{OL} = 24mA, V _{CCA} = 3V, V	V _{CCB} = 3V			0.65		
		I _{OL} = 32mA, V _{CCA} = 4.5V	', V _{CCB} = 4.5V			0.65		
	DIR at $V_I = V_{CCA}$ or GND,	$V_{CCA} = 1.65V \text{ to } 5.5V, V_{CC}$	T _A = 25°C			±1		
l _l	= 1.65V to 5.5V		$T_A = -40^{\circ}\text{C to } 125^{\circ}\text{C}$			±4	μA	
		A port at V _{CCA} = 0V,	T _A = 25°C			±1		
	\\ or\\ = 0 +0 5 5\\	$V_{CCB} = 0$ to 5.5V	$T_A = -40^{\circ}C \text{ to } 125^{\circ}C$			±10	μA	
l _{off}	V_I or $V_O = 0$ to 5.5V	B port at V _{CCA} = 0	T _A = 25°C		±			
		to 5.5V, V _{CCB} = 0V	$T_A = -40^{\circ}C \text{ to } 125^{\circ}C$			±10		
	A or B port at V _O = V _{CCO} o	r GND,	T _A = 25°C			±1		
l _{OZ}	$V_{CCA} = 1.65V \text{ to } 5.5V, V_{CC}$		T _A = -40°C to 125°C			±10	μA	
		V_{CCA} = 1.65V to 5.5V, V_{CCA}			10			
I _{CCA}	$V_I = V_{CCI}$ or GND, $I_O = 0$	$V_{CCA} = 5.5V$, $V_{CCB} = 0V$	V _{CCA} = 5.5V, V _{CCB} = 0V			4	μΑ	
		$V_{CCA} = 0V$, $V_{CCB} = 5.5V$				-10		
		$V_{CCA} = 1.65V \text{ to } 5.5V, V_{CCA}$			10			
I _{CCB}	$V_I = V_{CCI}$ or GND, $I_O = 0$	$V_{CCA} = 5.5V$, $V_{CCB} = 0V$	-10			μΑ		
		$V_{CCA} = 0V$, $V_{CCB} = 5.5V$			4			
I _{CCA} + I _{CCB}	$V_I = V_{CCI}$ or GND, $I_O = 0$, $V_{CCB} = 1.65V$ to 5.5V	/ _{CCA} = 1.65V to 5.5V,				20	μΑ	
A.I.	V _{CCA} = 3V to 5.5V,	A port at V _{CCA} – 0.6V, DI B port = open	R at V _{CCA} ,			50		
ΔI _{CCA}	V _{CCB} = 3V to 5.5V	DIR at V _{CCA} – 0.6V, B po A port at V _{CCA} or GND	ort = open,			50	μA	
ΔI _{CCB}	B port at V _{CCB} – 0.6V, DIR V _{CCB} = 3V to 5.5V	at GND, A port = open, V	CCA = 3V to 5.5V,			50	μΑ	
C _i	DIR at $V_I = V_{CCA}$ or GND,	T _A = 25°C, V _{CCA} = 3.3V, V	_{CCB} = 3.3V		2.5		pF	
C _{io}	A or B port at $V_O = V_{CCA/B}$ $V_{CCB} = 3.3V$	or GND, T _A = 25°C, V _{CCA}	= 3.3V,		6		pF	
			V _{CCA} = V _{CCB} = 1.8V		3			
		A-port input,	$V_{CCA} = V_{CCB} = 2.5V$	4				
		B-port output	V _{CCA} = V _{CCB} = 3.3V		4			
C (3)	$C_L = 0pF,$		V _{CCA} = V _{CCB} = 5V		4		<u>.</u> -	
C _{pdA} ⁽³⁾	f = 10MHz, $t_r = t_f = 1$ ns		V _{CCA} = V _{CCB} = 1.8V		18		pF	
		B-port input,	$V_{CCA} = V_{CCB} = 2.5V$		19			
		A-port output	$V_{CCA} = V_{CCB} = 3.3V$	20				
				21				

5.5 Electrical Characteristics (continued)

over operating free-air temperature range with all limits at $T_A = -40^{\circ}\text{C}$ to 125°C (unless otherwise noted)(1)(2)

PARAMETER		TEST CONDITIONS		MIN TYP	MAX	UNIT
			V _{CCA} = V _{CCB} = 1.8V	18		
		A-port input, B-port output	$V_{CCA} = V_{CCB} = 2.5V$	19		
	C _L = 0pF, f = 10MHz,		$V_{CCA} = V_{CCB} = 3.3V$	20		1
C _{pdB} (3)			V _{CCA} = V _{CCB} = 5V	21		рF
O _{pdB}	$t_r = t_f = 1$ ns		V _{CCA} = V _{CCB} = 1.8V	3		ρι
		B-port input,	$V_{CCA} = V_{CCB} = 2.5V$	4		
		A-port output	$V_{CCA} = V_{CCB} = 3.3V$	4		
			V _{CCA} = V _{CCB} = 5V	4		

- $\rm V_{CCO}$ is the $\rm V_{CC}$ associated with the output port. $\rm V_{CCI}$ is the $\rm V_{CC}$ associated with the input port. (1)
- (3) Power dissipation capacitance per transceiver

5.6 Switching Characteristics: V_{CCA} = 1.8V ±0.15V

over operating free-air temperature range (unless otherwise noted; see Figure 6-1)

PARAMETER	FROM	FROM (INPUT)	TO (OUTPUT)	V _{CCB} = ±0.15		V _{CCB} = ±0.2		V _{CCB} = ±0.3		V _{CCB} = ±0.5		UNIT
	(INPUT)	(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX		
t _{PLH}	А	В	3	20.7	2.2	13.3	1.7	11.3	1.4	10.2	ns	
t _{PHL}			2.8	17.3	2.2	11.5	1.8	10.1	1.7	10	115	
t _{PLH}	В	А	3	20.7	2.3	19	2.1	18.5	1.9	18.1	no	
t _{PHL}	В		2.8	17.3	2.1	15.9	2	15.6	1.8	15.2	ns	
t _{PHZ}	DIR	A	5.2	22.7	4.8	21.5	4.7	21.4	5.1	20.1	ne	
t_{PLZ}	DIK		2.3	13.5	2.1	13.5	2.4	13.7	3.1	13.9	ns	
t _{PHZ}	DIR	В	5.2	27.9	4.9	14.5	3.6	13.3	2.3	11.2	ns	
t _{PLZ}	DIK		4.2	19	2.2	12.2	2.3	11.4	2	9.4	115	
t _{PZH} ⁽¹⁾	DIR	А		39.7		31.2		29.9		27.5	no	
t _{PZL} ⁽¹⁾	DIK			45.2		30.4		28.9		26.4	ns	
t _{PZH} ⁽¹⁾	DID	В		34.2		26.8		25		24.1	ne	
t _{PZL} ⁽¹⁾	DIR	Ь		40.7		33		31.5		30.1	ns	

⁽¹⁾ The enable time is a calculated value, derived using the formula shown in Section 7.1.1.

5.7 Switching Characteristics: V_{CCA} = 2.5V ±0.2V

over operating free-air temperature range (unless otherwise noted; see Figure 6-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CCB} = ±0.15		V _{CCB} = ±0.2		V _{CCB} = ±0.3		V _{CCB} = ±0.5		UNIT
	(INPUT)	(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{PLH}	А	В	2.3	19	1.5	11.5	1.3	9.4	1.1	8.1	ns
t _{PHL}			2.1	15.9	1.4	10.5	1.3	8.4	0.9	7.6	115
t _{PLH}	В	А	2.2	13.3	1.5	11.5	1.4	11	1	10.5	ns
t _{PHL}	Б		2.2	11.5	1.4	10.7	1.3	10	0.9	9.2	115
t _{PHZ}	DIR	А	3	11.1	3.1	11.1	2.8	11.1	3.2	11.1	no
t _{PLZ}	DIR		1.3	8.9	1.3	8.9	1.3	8.9	1	8.8	ns
t _{PHZ}	DIR	В	5.2	26.7	4.1	14.4	3.9	13.2	2.4	10.1	no
t _{PLZ}) DIK	6	3.9	21.9	3.2	12.6	2.8	11.4	1.8	8.3	ns

Product Folder Links: SN74LVC1T45-Q1



5.7 Switching Characteristics: V_{CCA} = 2.5V ±0.2V (continued)

over operating free-air temperature range (unless otherwise noted; see Figure 6-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CCB} = 1.8V ±0.15V	V _{CCB} = 2.5V ±0.2V	V _{CCB} = 3.3V ±0.3V	V _{CCB} = 5V ±0.5V	UNIT
	(INPOT)	(001701)	MIN MAX	MIN MAX	MIN MAX	MIN MAX	
t _{PZH} (1)	DIR	А	35.2	24.1	22.4	18.8	ne
t _{PZL} (1)	DIK	DIK A	38.2	24.9	23.2	19.3	ns
t _{PZH} (1)	DIR	В	27.9	20.4	18.3	16.9	no
t _{PZL} ⁽¹⁾	DIR	В	27	21.6	19.5	18.7	ns

5.8 Switching Characteristics: $V_{CCA} = 3.3V \pm 0.3V$

over operating free-air temperature range (unless otherwise noted; see Figure 6-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CCB} = ±0.15		V _{CCB} = ±0.2		V _{CCB} = ±0.3		V _{CCB} = ±0.5		UNIT			
	(INPOT)	(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX				
t _{PLH}	Α	В	2.1	18.5	1.4	11	0.7	8.8	0.7	7.4	ne			
t _{PHL}			2	15.6	1.3	10	0.8	8	0.7	7	ns			
t _{PLH}	В	А	1.7	11.3	1.3	9.4	0.7	8.8	0.6	8.4	ne			
t _{PHL}		D	D		1.8	10.1	1.3	8.4	0.8	8	0.7	7.5	ns	
t _{PHZ}	DIR	NIP	DIB	A	2.9	10.3	3	10.3	2.8	10.3	3.4	10.3	ns	
t _{PLZ}			1.8	8.6	1.6	8.6	2.2	8.7	2.2	8.7	115			
t _{PHZ}	DID	DIR	В	5.4	27.5	3.9	13.1	2.9	11.8	2.4	9.8	ns		
t _{PLZ}	DIK		3.3	17.5	2.9	10.8	2.4	10.1	1.7	7.9	115			
t _{PZH} (1)	DIB	DIB	DIP	DIR	A		26.8		20.2		18.9		16.3	ns
t _{PZL} ⁽¹⁾	DIK			37.6		21.5		19.8		17.3	115			
t _{PZH} ⁽¹⁾	DIR	В		27.1		19.6		17.5		16.1	ns			
t _{PZL} (1)	DIK			25.9		20.3		18.3		17.3	115			

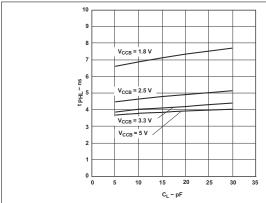
5.9 Switching Characteristics: $V_{CCA} = 5V \pm 0.5V$

over operating free-air temperature range (unless otherwise noted; see Figure 6-1)

PARAMETER	FROM	ROM TO (OUTPUT)		1.8V 5V	V _{CCB} = ±0.2		V _{CCB} = ±0.3		V _{CCB} = ±0.5		UNIT	
	(IIII OT)	(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX		
t _{PLH}	А	В	1.9	18.1	1	10.5	0.6	8.4	0.5	6.9	ne	
t _{PHL}	A	В	1.8	15.2	0.9	9.2	0.7	7.5	0.5	6.5	ns	
t _{PLH}	В	А	1.4	10.2	1	8.1	0.7	7.4	0.5	6.9	ns	
t _{PHL}	В	_ ^	1.7	10	0.9	7.6	0.7	7	0.5	6.5	115	
t _{PHZ}	DIR	NIP	А	2.1	8.4	2.2	8.4	2.2	8.5	2.2	8.4	ns
t _{PLZ}		_ ^	0.9	6.8	1	6.8	0.7	6.7	0.7	6.7	115	
t _{PHZ}	DID	DIR	В	4.8	26.2	2.5	14.8	1	11.5	2.5	9.5	ns
t _{PLZ}	DIK	В	3.2	17.8	2.5	10.4	2.5	10	1.6	7.5	115	
t _{PZH} (1)	DIR	NID	А		28		18.5		17.4		14.4	ns
t _{PZL} (1)	DIIX	_ ^		36.2		22.4		18.5		16	115	
t _{PZH} (1)	DID	В		24.9		17.3		15.1		13.6	20	
t _{PZL} ⁽¹⁾	DIR	ם		23.6		17.6		16		14.9	ns	

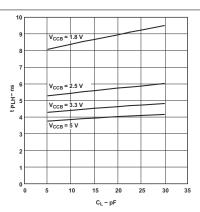


5.10 Typical Characteristics



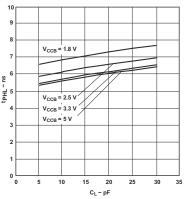
 $T_A = 25^{\circ}C, V_{CCA} = 1.8V$

Figure 5-1. Typical Propagation Delay (A to B) vs Load Capacitance



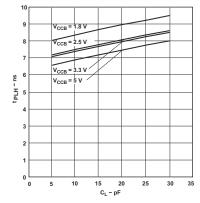
 $T_A = 25^{\circ}C, V_{CCA} = 1.8V$

Figure 5-2. Typical Propagation Delay (A to B) vs Load Capacitance



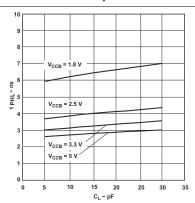
 $T_A = 25^{\circ}C, V_{CCA} = 1.8V$

Figure 5-3. Typical Propagation Delay (B to A) vs Load Capacitance



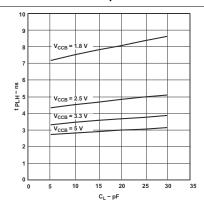
 $T_A = 25$ °C, $V_{CCA} = 1.8V$

Figure 5-4. Typical Propagation Delay (B to A) vs Load Capacitance



 $T_A = 25^{\circ}C, V_{CCA} = 2.5V$

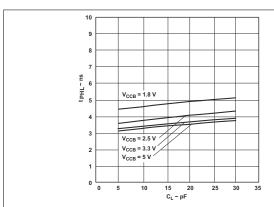
Figure 5-5. Typical Propagation Delay (A to B) vs Load Capacitance



 $T_A = 25$ °C, $V_{CCA} = 2.5V$

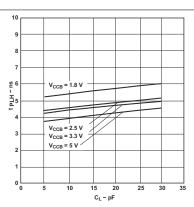
Figure 5-6. Typical Propagation Delay (A to B) vs Load Capacitance

5.10 Typical Characteristics (continued)



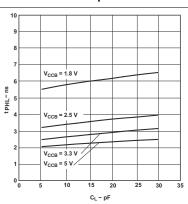
 $T_A = 25^{\circ}C, V_{CCA} = 2.5V$

Figure 5-7. Typical Propagation Delay (B to A) vs Load Capacitance



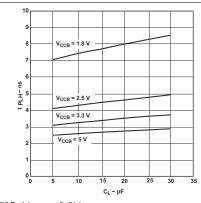
 $T_A = 25^{\circ}C, V_{CCA} = 2.5V$

Figure 5-8. Typical Propagation Delay (B to A) vs Load Capacitance



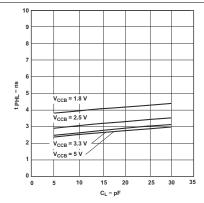
 $T_A = 25^{\circ}C, V_{CCA} = 3.3V$

Figure 5-9. Typical Propagation Delay (A to B)
vs Load Capacitance



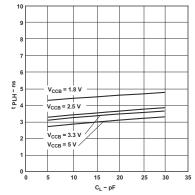
$$T_A = 25^{\circ}C, V_{CCA} = 3.3V$$

Figure 5-10. Typical Propagation Delay (A to B) vs Load Capacitance



 $T_A = 25^{\circ}C, V_{CCA} = 3.3V$

Figure 5-11. Typical Propagation Delay (B to A) vs Load Capacitance

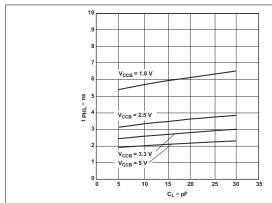


 $T_A = 25^{\circ}C, V_{CCA} = 3.3V$

Figure 5-12. Typical Propagation Delay (B to A) vs Load Capacitance

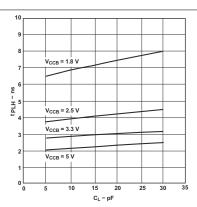


5.10 Typical Characteristics (continued)



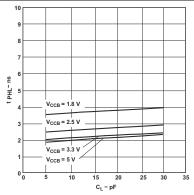
 $T_A = 25^{\circ}C$, $V_{CCA} = 5V$

Figure 5-13. Typical Propagation Delay (A to B) vs Load Capacitance



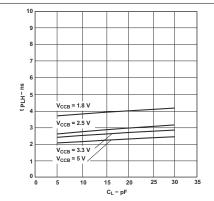
 $T_A = 25^{\circ}C, V_{CCA} = 5V$

Figure 5-14. Typical Propagation Delay (A to B) vs Load Capacitance



 $T_A = 25$ °C, $V_{CCA} = 5V$

Figure 5-15. Typical Propagation Delay (B to A) vs Load Capacitance



 $T_A = 25$ °C, $V_{CCA} = 5V$

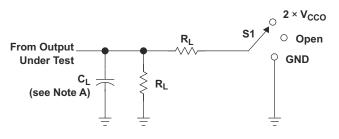
Figure 5-16. Typical Propagation Delay (B to A) vs Load Capacitance

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 $\mathbf{V}_{\mathsf{CCA}}$

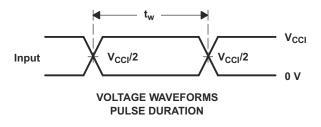
Parameter Measurement Information



TEST	S 1
t _{pd}	Open
t _{PLZ} /t _{PZL}	2 × V _{CCO}
t _{PHZ} /t _{PZH}	GND

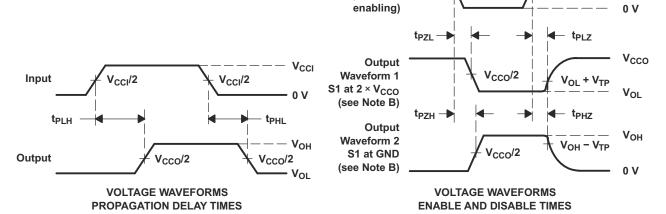
LOAD CIRCUIT

V _{CCO}	CL	R _L	V _{TP}
1.8 V ± 0.15 V	15 pF	2 k Ω	0.15 V
2.5 V ± 0.2 V	15 pF	2 k Ω	0.15 V
3.3 V ± 0.3 V	15 pF	2 k Ω	0.3 V
5 V ± 0.5 V	15 pF	2 k Ω	0.3 V



V_{CCA}/2

V_{CCA}/2



Output Control

(low-level

- NOTES: A. C_I includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_0 = 50 \Omega$, $dv/dt \geq$ 1 V/ns.
 - D. The outputs are measured one at a time, with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
 - F. $\,t_{PZL}$ and t_{PZH} are the same as $t_{en}.$
 - G. t_{PLH} and t_{PHL} are the same as t_{pd} .
 - H. V_{CCI} is the V_{CC} associated with the input port.
 - I. V_{CCO} is the V_{CC} associated with the output port.
 - J. All parameters and waveforms are not applicable to all devices.

Figure 6-1. Load Circuit and Voltage Waveforms

6 Detailed Description

6.1 Overview

The SN74LVC1T45-Q1 is single-bit, dual-supply, non-inverting voltage level translation. Pin A and that direction control pin (DIR) are supported by V_{CCA} and pin B is supported by V_{CCB} . The A port can accept I/O voltages ranging from 1.65V to 5.5V, while the B port can accept I/O voltages from 1.65V to 5.5V. The high on the DIR allows data transmissions from A to B and a low on the DIR allows data transmissions from B to A.

6.2 Functional Block Diagram

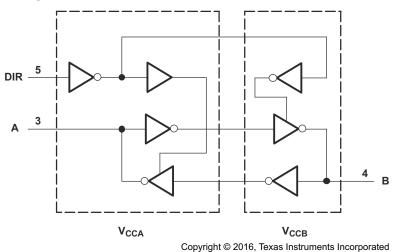


Figure 6-1. Logic Diagram (Positive Logic)

6.3 Feature Description

The SN74LVC1T45-Q1 has a fully configurable dual-rail design that allows each port to operate over the full 1.65V to 5.5V power-supply range. Both V_{CCA} and V_{CCB} can be supplied at any voltage between 1.65V and 5.5V, making the device suitable for translating between any of the voltage nodes (1.8V, 2.5V, 3.3V, and 5V).

SN74LVC1T45-Q1 can support high data rate applications. The translated signal data rate can be up to 420Mbps when the signal is translated from 3.3V to 5V.

loff prevents backflow current by disabling I/O output circuits when device is in partial-power-down mode.

6.3.1 Glitch-Free Power Supply Sequencing

Either supply rail may be powered on or off in any order without producing a glitch on the I/Os (that is, where the output erroneously transitions to VCC when it should be held low or vice versa). Glitches of this nature can be misinterpreted by a peripheral as a valid data bit, which could trigger a false device reset of the peripheral, a false device configuration of the peripheral, or even a false data initialization by the peripheral.

6.4 Device Functional Modes

Table 6-1 lists the operational modes of SN74LVC1T45-Q1.

Table 6-1. Function Table⁽¹⁾

INPUT DIR	OPERATION
L	B data to A bus
Н	A data to B bus

(1) Input circuits of the data I/Os always are active.

Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

1 Application Information

The SN74LVC1T45-Q1 device can be used in level-translation applications for interfacing devices or systems operating at different interface voltages with one another. The maximum data rate can be up to 420Mbps when device translates signals from 3.3V to 5V.

1.1 Enable Times

Calculate the enable times for the SN74LVC1T45-Q1 using the following formulas:

- t_{PZH} (DIR to A) = t_{PLZ} (DIR to B) + t_{PLH} (B to A)
- t_{PZL} (DIR to A) = t_{PHZ} (DIR to B) + t_{PHL} (B to A)
- t_{PZH} (DIR to B) = t_{PLZ} (DIR to A) + t_{PLH} (A to B)
- t_{P7I} (DIR to B) = t_{PH7} (DIR to A) + t_{PHI} (A to B)

In a bidirectional application, these enable times provide the maximum delay from the time the DIR bit is switched until an output is expected. For example, if the SN74LVC1T45-Q1 initially is transmitting from A to B, then the DIR bit is switched; the B port of the device must be disabled before presenting it with an input. After the B port has been disabled, an input signal applied to it appears on the corresponding A port after the specified propagation delay.

2 Typical Applications

2.1 Unidirectional Logic Level-Shifting Application

Figure 7-1 shows an example of the SN74LVC1T45-Q1 being used in a unidirectional logic level-shifting application.

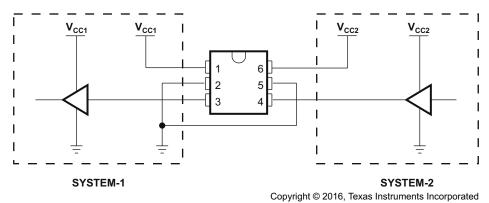


Figure 7-1. Unidirectional Logic Level-Shifting Application

2.1.1 Design Requirements

For this design example, use the parameters listed in Table 7-1.

Table 7-1. Design Parameters

rable 7 1: Design rarameters							
PARAMETER	VALUE						
Input voltage	1.65V to 5.5V						
Output voltage	1.65V to 5.5V						

2.1.2 Detailed Design Procedure

To begin the design process, determine the following:

- · Input voltage range
 - Use the supply voltage of the device that is driving the SN74LVC1T45-Q1 device to determine the input voltage range. For a valid logic high the value must exceed the VIH of the input port. For a valid logic low the value must be less than the VIL of the input port.
- · Output voltage range
 - Use the supply voltage of the device that the SN74LVC1T45-Q1 device is driving to determine the output voltage range.

2.1.3 Application Curves

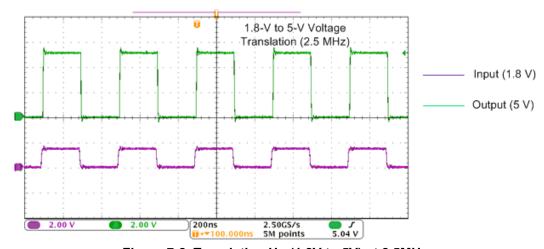


Figure 7-2. Translation Up (1.8V to 5V) at 2.5MHz

2.2 Bidirectional Logic Level-Shifting Application

Figure 7-3 shows the SN74LVC1T45-Q1 being used in a bidirectional logic level-shifting application. Because the SN74LVC1T45-Q1 does not have an output-enable (OE) pin, the system designer should take precautions to avoid bus contention between SYSTEM-1 and SYSTEM-2 when changing directions.

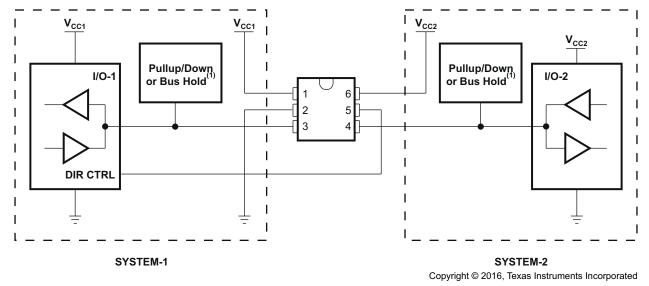


Figure 7-3. Bidirectional Logic Level-Shifting Application

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2.2.1 Detailed Design Procedure

Table 7-2 shows data transmission from SYSTEM-1 to SYSTEM-2 and then from SYSTEM-2 to SYSTEM-1.

Table	e 7-2	Data	Trans	mission

STATE	DIR CTRL	I/O-1	I/O-2	DESCRIPTION
1	Н	Out	In	SYSTEM-1 data to SYSTEM-2
2	Н	Hi-Z	Hi-Z	SYSTEM-2 is getting ready to send data to SYSTEM-1. I/O-1 and I/O-2 are disabled. The bus-line state depends on pullup or pulldown. ⁽¹⁾
3	L	Hi-Z	Hi-Z	DIR bit is flipped. I/O-1 and I/O-2 still are disabled. The bus-line state depends on pullup or pulldown. ⁽¹⁾
4	L	Out	In	SYSTEM-2 data to SYSTEM-1

(1) SYSTEM-1 and SYSTEM-2 must use the same conditions, that is, both pullup or both pulldown.

2.2.2 Application Curves

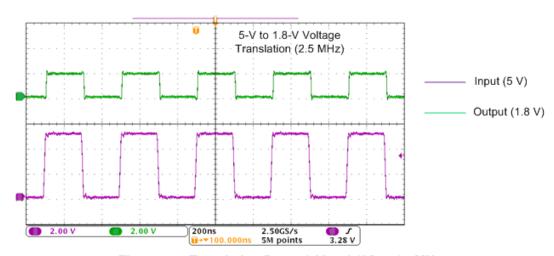


Figure 7-4. Translation Down (5V to 1.8V) at 2.5MHz

3 Power Supply Recommendations

Always apply a ground reference to the GND pins first. This device is designed for glitch free power sequencing without any supply sequencing requirements such as ramp order or ramp rate.

This device was designed with various power supply sequencing methods in mind to help prevent unintended triggering of downstream devices, as described in *Glitch-free Power Supply Sequencing*.

4 Layout

4.1 Layout Guidelines

For device reliability, the following common printed-circuit board layout guidelines are recommended:

- Bypass capacitors must be used on power supplies.
- Short trace lengths must be used to avoid excessive loading.
- Placing pads on the signal paths for loading capacitors or pullup resistors to help adjust rise and fall times of signals depends on the system requirements.

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4.2 Layout Example



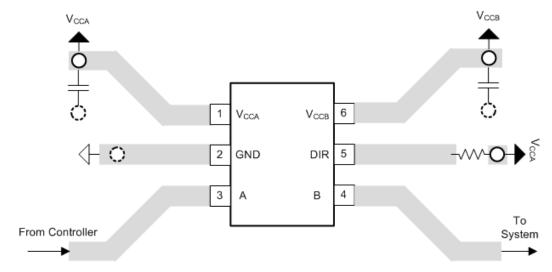


Figure 7-5. Layout Schematic



7 Device and Documentation Support

7.1 Documentation Support

7.1.1 Related Documentation

For related documentation see the following:

Texas Instruments, Implications of Slow or Floating CMOS Inputs application note

7.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

7.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

7.4 Trademarks

TI E2E[™] is a trademark of Texas Instruments.

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7.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

7.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

8 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Ona	anges from Revision E (December 2022) to Revision F (June 2024)	Page
• (Jpdated Package Information table to include package lead size	1
٠ ر	Jpdated the Power Supply Recommendations section	15
Cha	anges from Revision D (July 2017) to Revision E (December 2022)	Page
	anges from Revision D (July 2017) to Revision E (December 2022) Jpdated the numbering format for tables, figures, and cross-references throughout the document	
• [• • • • • • • • • • • • • • • • • • • •	1

9 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com 23-May-2025

PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
SN74LVC1T45QDCKRQ1	Active	Production	SC70 (DCK) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	5TR
SN74LVC1T45QDCKRQ1.A	Active	Production	SC70 (DCK) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	5TR
SN74LVC1T45QDCKRQ1.B	Active	Production	SC70 (DCK) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	5TR

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74LVC1T45-Q1:

Catalog: SN74LVC1T45

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No. RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

PACKAGE OPTION ADDENDUM

www.ti.com 23-May-2025

● Enhanced Product : SN74LVC1T45-EP

NOTE: Qualified Version Definitions:

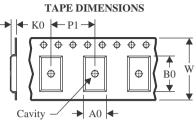
- Catalog TI's standard catalog product
- Enhanced Product Supports Defense, Aerospace and Medical Applications

PACKAGE MATERIALS INFORMATION

www.ti.com 11-Apr-2024

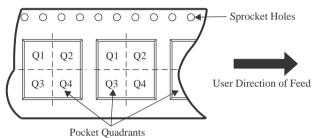
TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

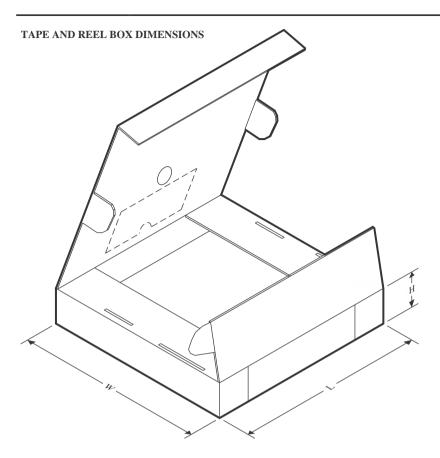


*All dimensions are nominal

Device	U	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC1T45QDCKRQ1	SC70	DCK	6	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3

PACKAGE MATERIALS INFORMATION

www.ti.com 11-Apr-2024

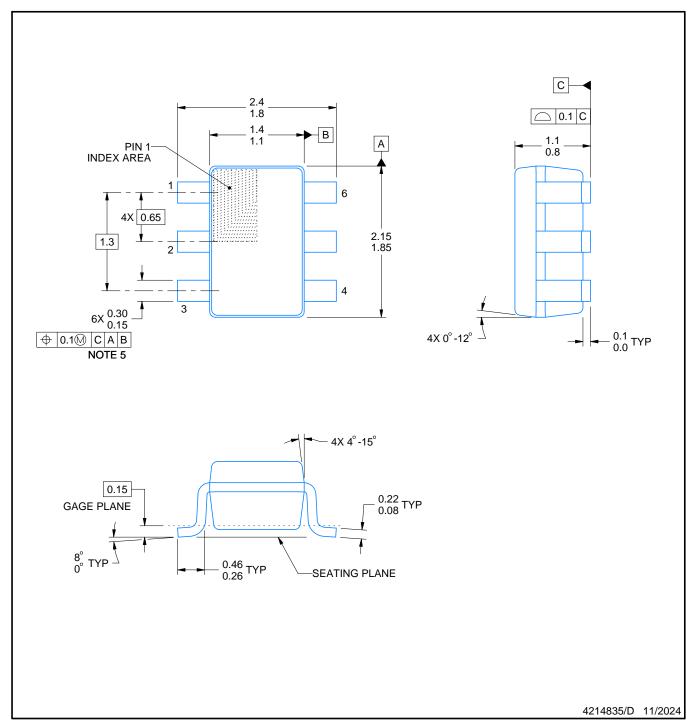


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
SN74LVC1T45QDCKRQ1	SC70	DCK	6	3000	202.0	201.0	28.0	



SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

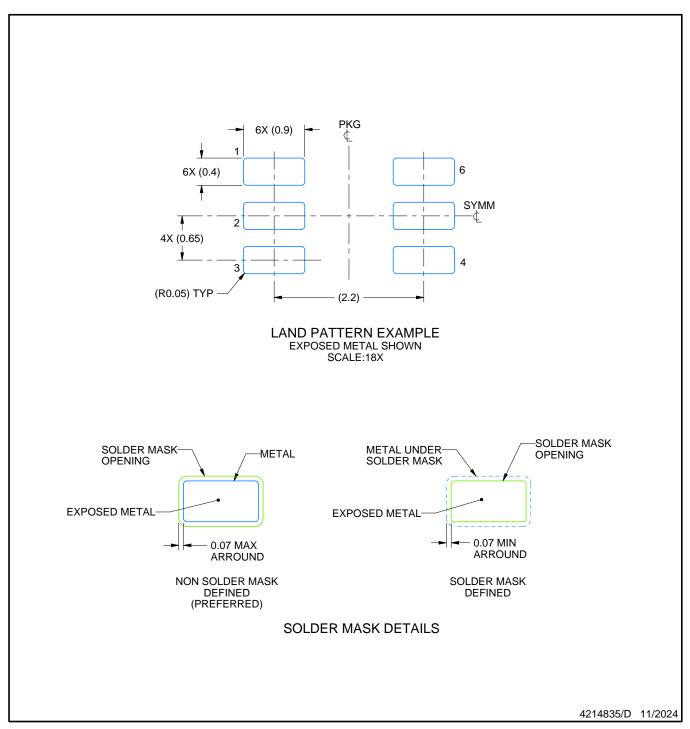
 2. This drawing is subject to change without notice.

 3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.

 4. Falls within JEDEC MO-203 variation AB.



SMALL OUTLINE TRANSISTOR



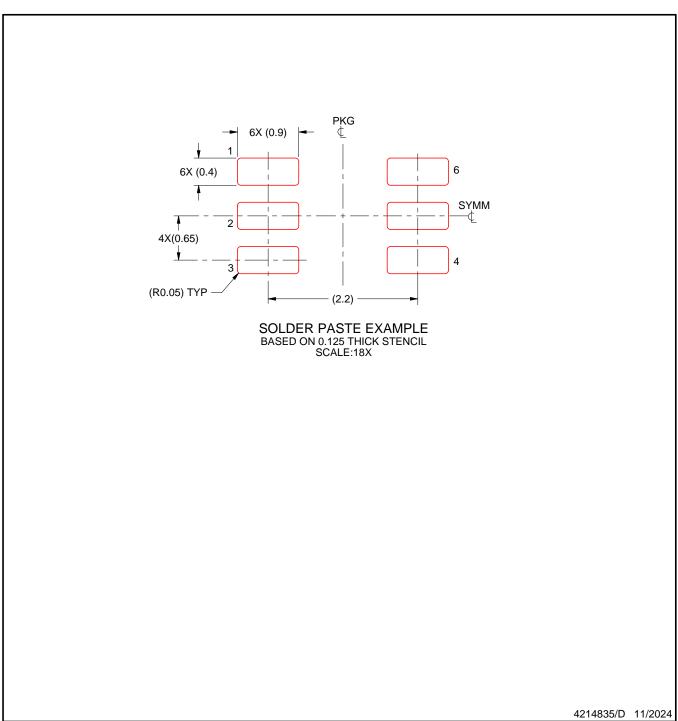
NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.



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